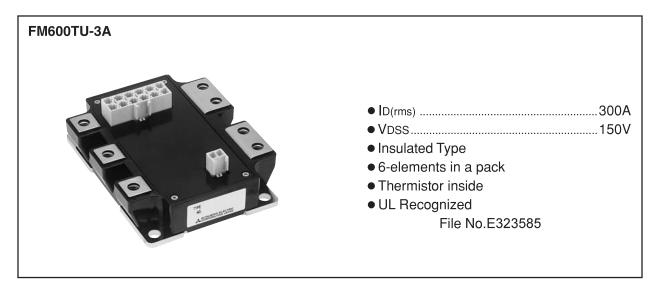
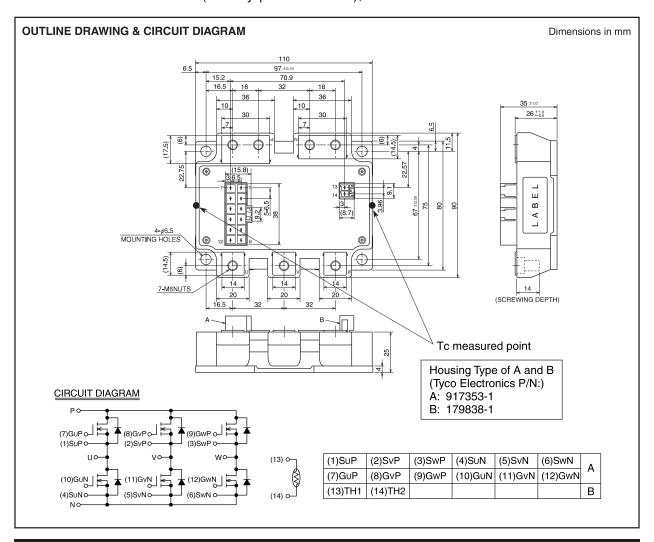
HIGH POWER SWITCHING USE INSULATED PACKAGE



APPLICATION

AC motor control of forklift (battery power source), UPS



HIGH POWER SWITCHING USE **INSULATED PACKAGE**

ABSOLUTE MAXIMUM RATINGS (Tj = 25°C unless otherwise specified.)

Symbol	Item	Conditions	Rating	Unit
VDSS	Drain-source voltage	G-S Short	150	V
Vgss	Gate-source voltage	D-S Short	±20	V
lo	Drain current	$Tc' = 114^{\circ}C^{*3}$	300	Α
lом	Torain current	Pulse*2	600	Α
IDA	Avalanche current	$L = 10\mu H \text{ Pulse}^{2}$	300	Α
Is*1	Course current		300	Α
Ism*1	Source current	Pulse*2	600	Α
Po*4	Maying up a guar diaginatian	Tc = 25°C	960	W
Po* ⁴	Maximum power dissipation	$Tc' = 25^{\circ}C^{*3}$	1300	W
Tch	Channel temperature		-40 ~ +150	°C
Tstg	Storage temperature		-40 ~ +125	°C
Visol	Isolation voltage	Main terminal to base plate, AC 1 min, f=60Hz, RMS	2500	V
_	Mounting torque	Main Terminal M6	3.5 ~ 4.5	N∙m
		Mounting to heat sink M6	3.5 ~ 4.5	N∙m
	Weight	Typical value	600	g

ELECTRICAL CHARACTERISTICS (Tj = 25° C unless otherwise specified.)

Symbol	Item	Conditions		Limits			Unit
				Min.	Тур.	Max.	Unit
IDSS	Drain cutoff current	VDS = VDSS, VGS = 0V		_	_	1	mA
VGS(th)	Gate-source threshold voltage	ID = 30mA, VDS = 10V		4.7	6	7.3	V
Igss	Gate leakage current	VGS = VGSS, VDS = 0V		_	_	1.5	μΑ
rDS(on)	Static drain-source	ID = 300A T _j = 25°C		_	1.6	2.2	
(chip)	On-state resistance	VGS = 15V	Tj = 125°C	_	3.0	_	mΩ
VDS(on)	Static drain-source	ID = 300A	Tj = 25°C	_	0.48	0.66	V
(chip)	On-state voltage	VGS = 15V	Tj = 125°C	_	0.91	_	
RDD'-SS'	Internal lead resistance	ID = 300A	Tj = 25°C	_	0.7	_	- mΩ
		terminal-chip	Tj = 125°C	_	1.0	_	
Ciss	Input capacitance	VDS = 10V VGS = 0V VDD = 80V, ID = 300A, VGS = 15V		_	_	110	nF
Coss	Output capacitance			_	_	15	
Crss	Reverse transfer capacitance			_	_	10	
Qg	Total gate charge			_	1950	_	nC
td(on)	Turn-on delay time	$VDD = 80V, ID = 300A, VGS1 = VGS2 = 15V$ $RG = 4.2\Omega, Inductive load switching operation IS = 300A$		_	_	400	- ns
tr	Rise time			_	_	400	
td(off)	Turn-off delay time			_	_	500	
tf	Fall time			_	_	400	
trr*1	Reverse recovery time			_	_	200	ns
Qrr*1	Reverse recovery charge			_	8.0	_	μС
Vsp*1	Source-drain voltage	Is = 300A, VGS = 0V		_	_	1.3	V
Rth(j-c)	Thermal resistance	MOSFET part (1/6 module)*7		_	_	0.13	
Rth(j-c')	- Thermal resistance	MOSFET part (1/6 module)*3		_	_	0.096	k/w
Rth(c-s)	Contact thermal resistance	Case to fin, Thermal grease Applied*8 (1/6 module)		_	0.1	_] '`'
Rth(c'-s')	Contact thermal resistance Case to fin, Thermal grease Applied* ^{3, *8} (1/6 module)			0.09			

NTC THERMISTOR PART

Symbol	Parameter	Conditions	Limits			I India
			Min.	Тур.	Max.	Unit
R ₂₅ *6	Resistance	$TTH = 25^{\circ}C^{*5}$	_	100	_	kΩ
B*6	B Constant	Resistance at TTH = 25°C, 50°C*5		4000		K

^{*7:} Tc measured point is shown in page OUTLINE DRAWING. *8: Typical value is measured by using thermally conductive grease of λ =0.9 W/(m·K).



^{*11:} It is characteristics of the anti-parallel, source to drain free-wheel diode (FWDi).
*2: Pulse width and repetition rate should be such that the device junction temperature (Tj) does not exceed Tj max rating.

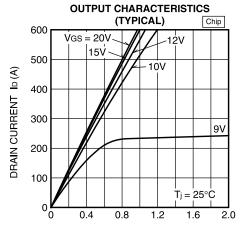
^{*3:} Tc' measured point is just under the chips. If use this value, Rth(s-a) should be measured just under the chips. *4: Pulse width and repetition rate should be such as to cause negligible temperature rise.

^{*5:} TTH is thermistor temperature.

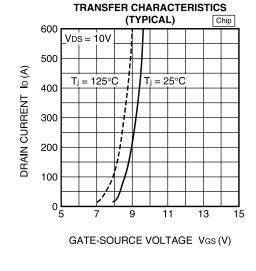
^{*6:} B = (InR1-InR2)/(1/T1-1/T2) R1: Resistance at T1(K), R2: Resistance at T2(K)

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PERFORMANCE CURVES

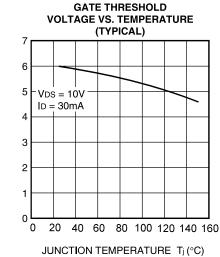


DRAIN-SOURCE VOLTAGE VDS (V)

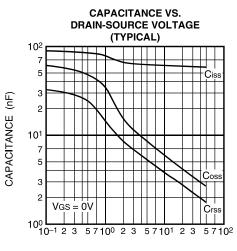


DRAIN-SOURCE ON-STATE VOLTAGE VS. TEMPERATURE (TYPICAL) Chip ID = 300ADRAIN-SOURCE ON-STATE RESISTANCE $^{(On)}$ (m Ω) 3.5 3.0 Vgs = 15V 2.5 2.0 1.5 1.0 0.5 0 40 60 80 100 120 140 160 JUNCTION TEMPERATURE Tj (°C)

GATE THRESHOLD VOLTAGE VGS(th) (V) 6 5 3 2



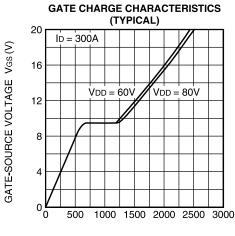
DRAIN-SOURCE ON-STATE VOLTAGE VS. GATE BIAS (TYPICAL) Chip Ti = 25°C DRAIN-SOURCE ON-STATE VOLTAGE VDS(on) (V) 2.5 2.0 1.5 ID = 600A1.0 ID = 300A0.5 0 L ID = 150A12 16 GATE-SOURCE VOLTAGE Vgs (V)

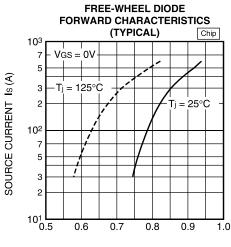


DRAIN-SOURCE VOLTAGE VDS (V)

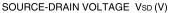


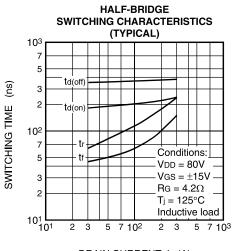
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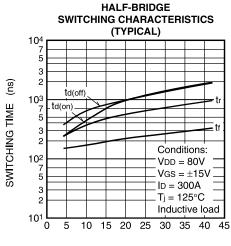




GATE CHARGE QG (nC)

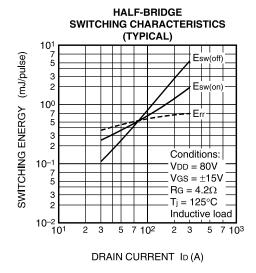


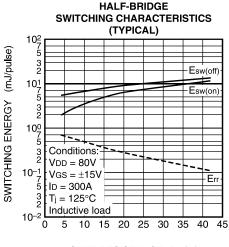




DRAIN CURRENT ID (A)



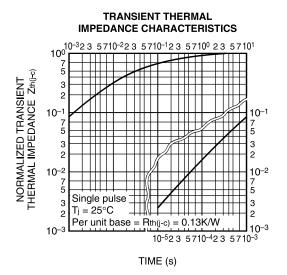




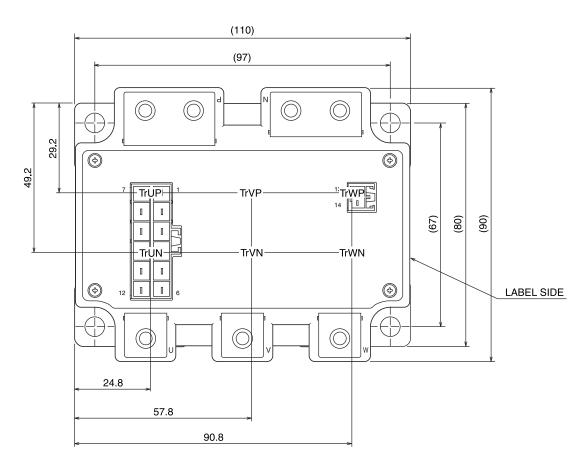
GATE RESISTANCE $\,\operatorname{Rg}\,(\Omega)$

HIGH POWER SWITCHING USE INSULATED PACKAGE

REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL) 10³ 3 102 Irr (A), trr (ns) 5 Conditions: 10<u>1</u> VDD = 80V Vgs = ±15V $RG = 4.2\Omega$ 3 Tj = 25°C Inductive load 100 L 2 3 5 7 102 2 5 7 10³ SOURCE CURRENT Is (A)



CHIP LAYOUT



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